

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

# TLP627, TLP627-2, TLP627-4

PROGRAMMABLE CONTROLLERS.  
DC - OUTPUT MODULE.  
TELECOMMUNICATION.

The TOSHIBA TLP627, -2, and -4 consist of a gallium arsenide infrared emitting diode optically coupled to a darlington connected phototransistor which has an integral base-emitter resistor to optimize switching speed and elevated temperature characteristics.

The TLP627-2 offers two isolated channels in a eight lead plastic DIP, while the TLP627-4 provide four isolated channels per package.

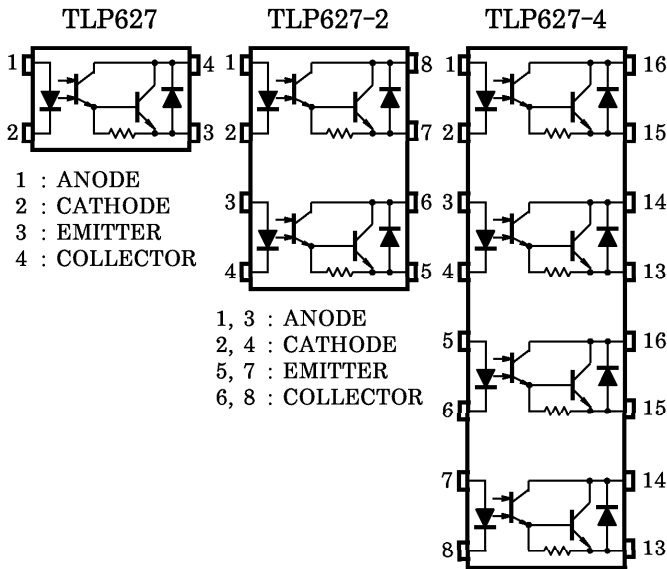
- Collector-Emitter Voltage : 300V (Min.)
- Current Transfer Ratio : 1000% (Min.)
- Isolation Voltage : 5000Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

	MADE IN JAPAN		MADE IN THAILAND	
UL Recognized	E67349	*1	E152349	*1
BSI Approved	7426, 7427	*2	7426, 7427	*2

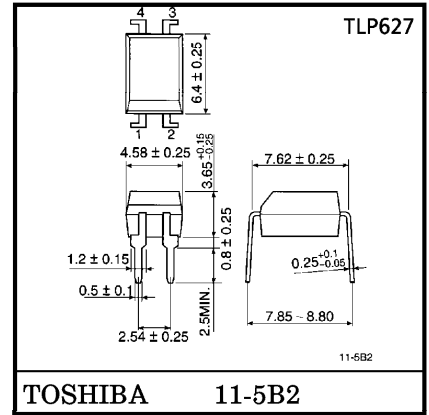
\*1 UL1577

\*2 BS EN60065 : 1994, BS EN60950 : 1992

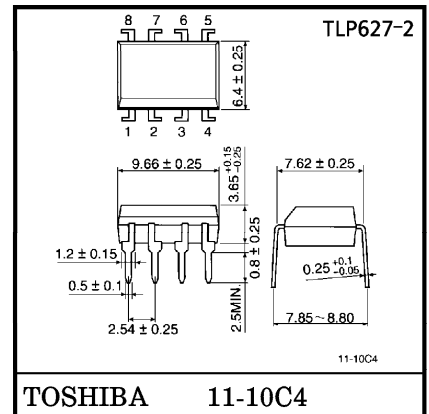
PIN CONFIGURATIONS (TOP VIEW)



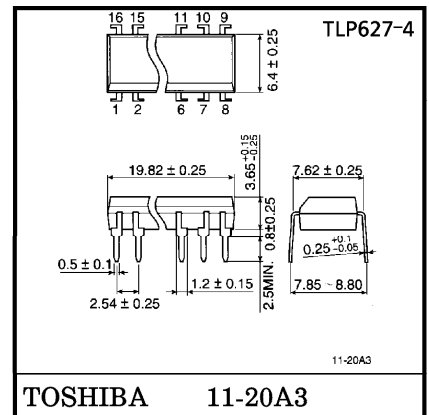
Unit in mm



Weight : 0.26g



Weight : 0.54g



Weight : 1.1g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			TLP627	TLP627-2 TLP627-4	
LED	Forward Current	I <sub>F</sub>	60	50	mA
	Forward Current Derating	ΔI <sub>F</sub> /°C	-0.7 (Ta ≥ 39°C)	-0.5 (Ta ≥ 25°C)	mA/°C
	Pulse Forward Current	I <sub>FP</sub>	1 (100μs pulse, 100pps)		A
	Power Dissipation (1 Circuit)	P <sub>D</sub>	100	70	mW
	Power Dissipation Derating (Ta ≥ 25°C, 1 Circuit)	ΔP <sub>D</sub> /°C	-1.0	-0.7	mW/°C
	Reverse Voltage	V <sub>R</sub>	5		V
	Junction Temperature	T <sub>j</sub>	125		°C
DETECTOR	Collector-Emitter Voltage	V <sub>CEO</sub>	300		V
	Emitter-Collector Voltage	V <sub>ECO</sub>	0.3		V
	Collector Current	I <sub>C</sub>	150		mA
	Collector Power Dissipation (1 Circuit)	P <sub>C</sub>	150 (*300)	100	mW
	Collector Power Dissipation Derating (Ta ≥ 25°C, 1 Circuit)	ΔP <sub>C</sub> /°C	-1.5 (*-3.5)	-1.0	mW/°C
	Junction Temperature	T <sub>j</sub>	125		°C
Storage Temperature Range		T <sub>stg</sub>	-55~125		°C
Operating Temperature Range		T <sub>opr</sub>	-55~100		°C
Lead Soldering Temperature		T <sub>sold</sub>	260 (10sec)		°C
Total Package Power Dissipation (1 Circuit)		P <sub>T</sub>	250 (*320)	150	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C, 1 Circuit)		ΔP <sub>T</sub> /°C	-2.5 (*-3.2)	-1.5	mW/°C
Isolation Voltage		BV <sub>S</sub>	5000 (AC, 1min., R.H. ≤ 60%)		V <sub>rms</sub>

\* I<sub>F</sub> = 20mA Max

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>CC</sub>	—	—	200	V
Forward Current	I <sub>F</sub>	—	16	25	mA
Collector Current	I <sub>C</sub>	—	—	120	mA
Operating Temperature	T <sub>opr</sub>	-25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$V_F$	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	$I_R$	$V_R = 5\text{V}$	—	—	10	$\mu\text{A}$
	Capacitance	$C_T$	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}$	300	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	0.3	—	—	V
	Collector Dark Current	$I_{CEO}$	$V_{CE} = 200\text{V}$	—	10	200	nA
			$V_{CE} = 200\text{V}, T_a = 85^\circ\text{C}$	—	—	20	$\mu\text{A}$
Capacitance Collector to Emitter	$C_{CE}$	$V = 0, f = 1\text{MHz}$	—	10	—	pF	

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	$I_C / I_F$	$I_F = 1\text{mA}, V_{CE} = 1\text{V}$	1000	4000	—	%
Saturated CTR	$I_C / I_F(\text{sat})$	$I_F = 10\text{mA}, V_{CE} = 1\text{V}$	500	—	—	%
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 10\text{mA}, I_F = 1\text{mA}$	—	—	1.0	V
		$I_C = 100\text{mA}, I_F = 10\text{mA}$	0.3	—	1.2	

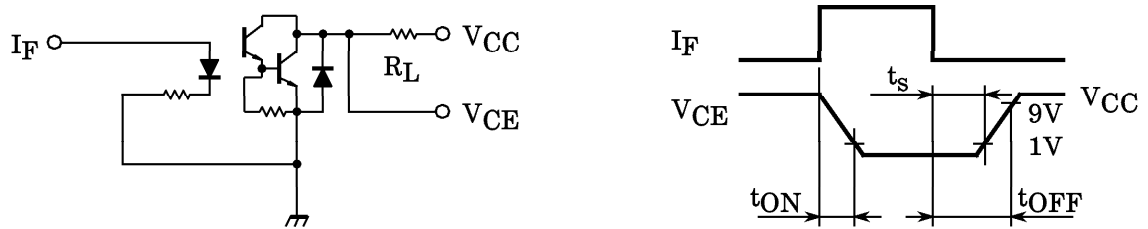
ISOLATION CHARACTERISTICS (Ta = 25°C)

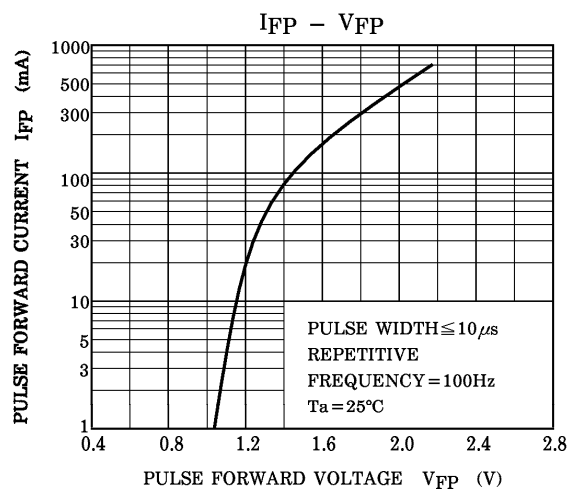
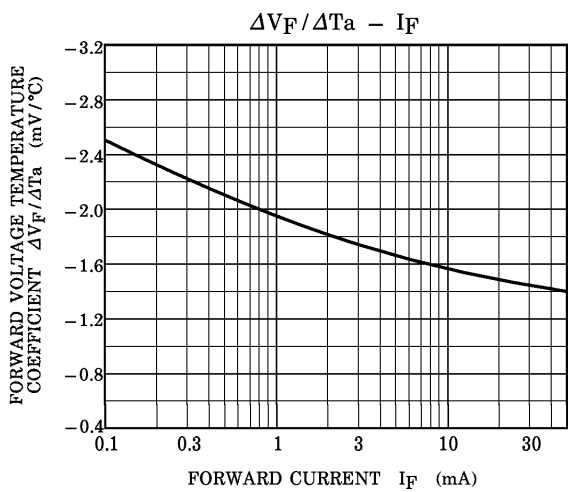
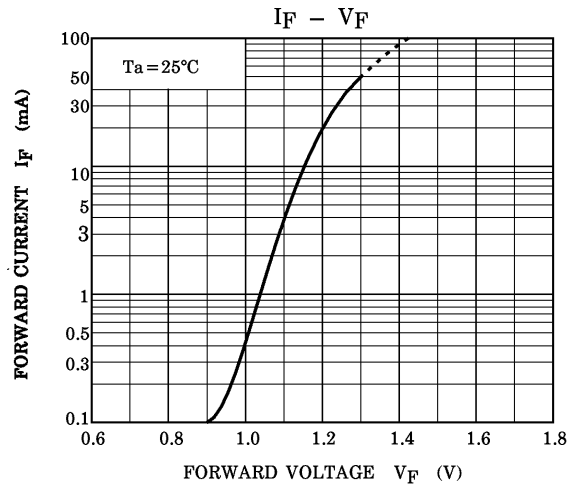
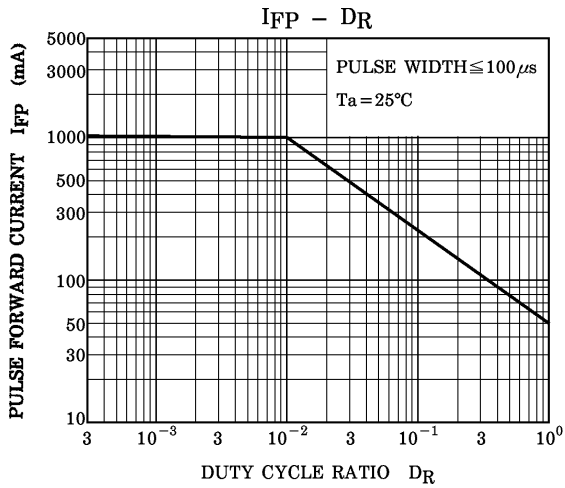
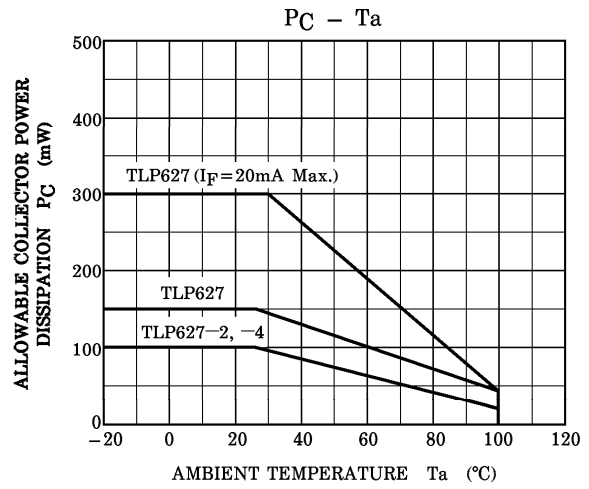
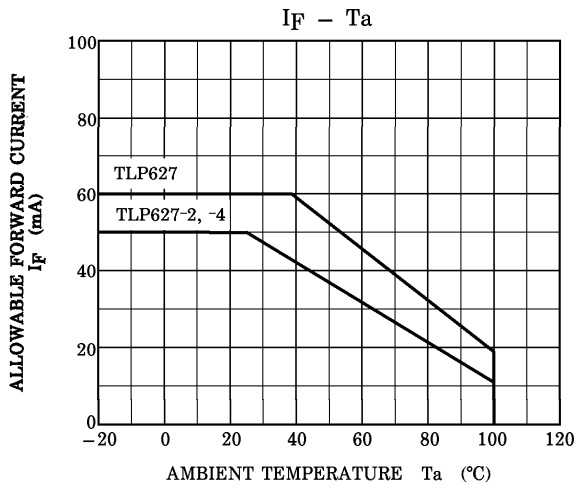
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	$C_S$	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	$R_S$	$V_S = 500\text{V R.H.} \leq 60\%$	$5 \times 10^{10}$	$10^{14}$	—	$\Omega$
Isolation Voltage	$BV_S$	AC, 1 minute	5000	—	—	$V_{\text{rms}}$
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc

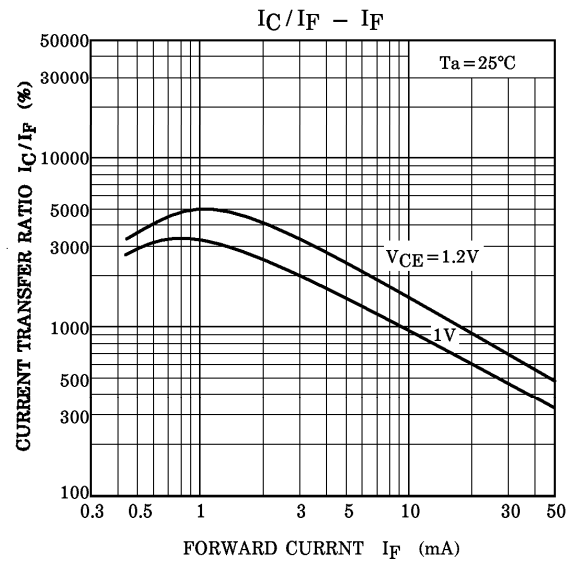
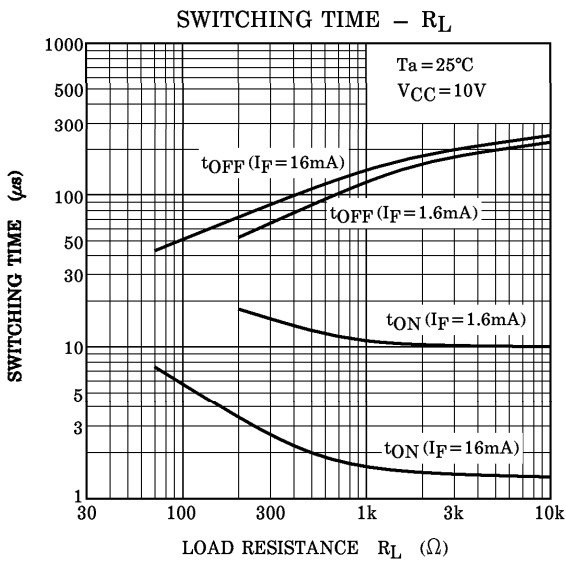
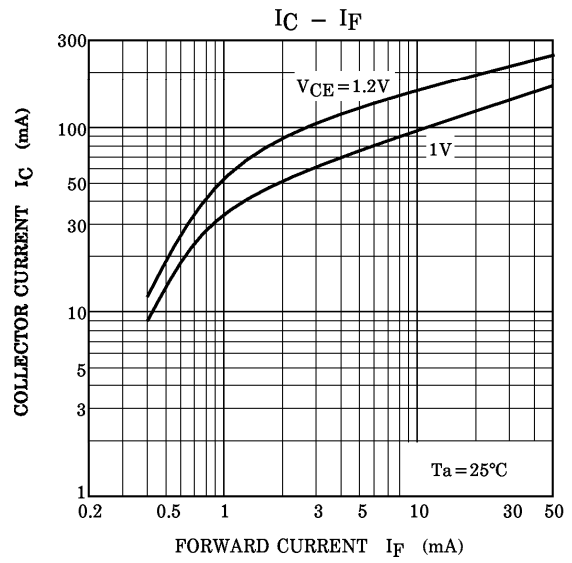
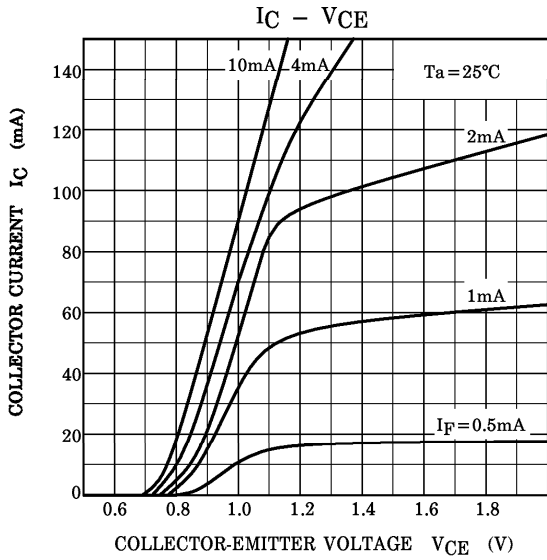
SWITCHING CHARACTERISTICS (Ta = 25°C)

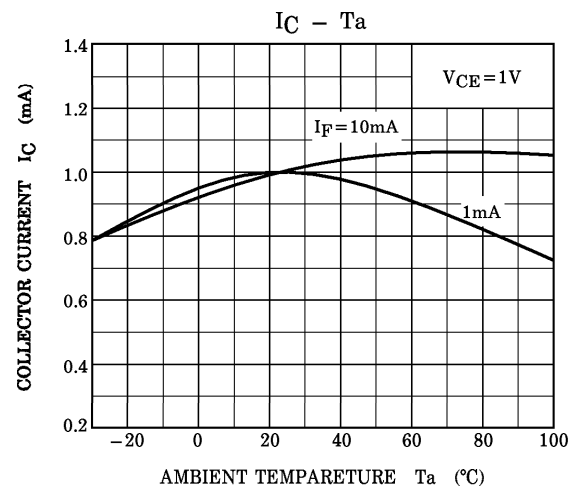
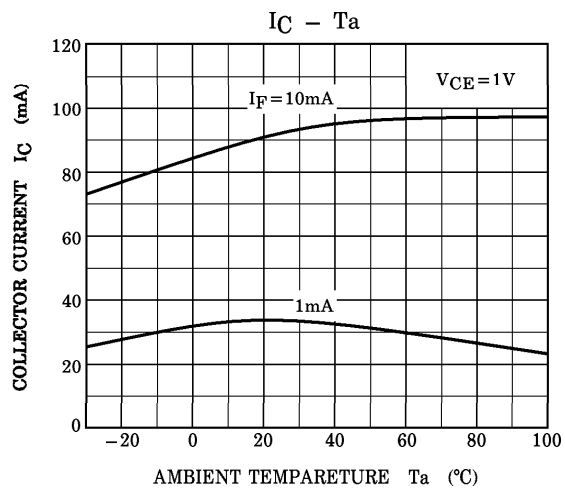
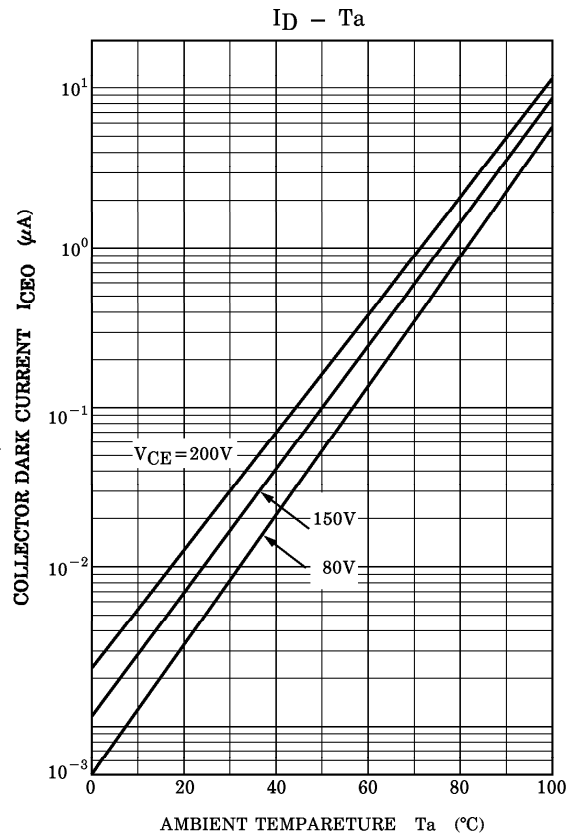
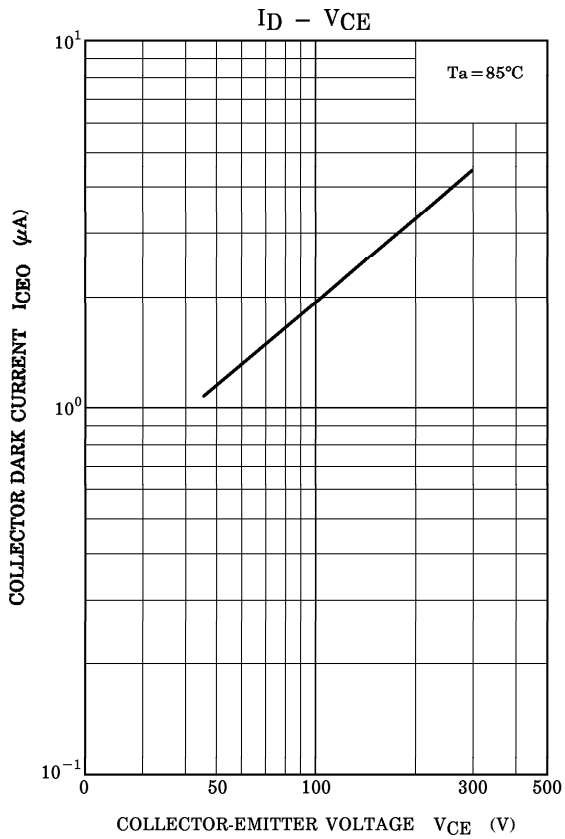
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	$t_r$	$V_{CC} = 10V$ $I_C = 10mA$ $R_L = 100\Omega$	—	40	—	$\mu s$
Fall Time	$t_f$		—	15	—	
Turn-on Time	$t_{on}$		—	50	—	
Turn-off Time	$t_{off}$		—	15	—	
Turn-on Time	$t_{ON}$	$R_L = 180\Omega$ (Fig.1) $V_{CC} = 10V, I_F = 16mA$	—	5	—	$\mu s$
Strage Time	$t_s$		—	40	—	
Tuen-off Time	$t_{OFF}$		—	80	—	

Fig.1 SWITCHING TIME TEST CIRCUIT









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